



S/N 10/081818

PATENTIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jerome M. Eldridge et al. Examiner: Tu-Tu Ho
Serial No.: 10/081818 Group Art Unit: 2818
Filed: February 20, 2002 Docket: 1303.045US1
Title: ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW
ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS

#13
I.D.J.
G. Stang
8-19-04

INFORMATION DISCLOSURE STATEMENT

MS RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. § 1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

JEROME M. ELDRIDGE ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
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Date

13 May '04

By

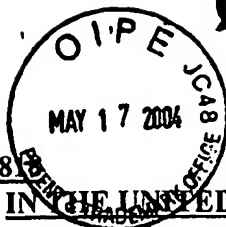
Timothy B Clise
Reg. No. 40,957

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 13th day of May, 2004.

Name

Amy Moriarty

Signature



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PATENT

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Examiner: Tu-Tu Ho

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Title: ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW
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COMMUNICATION CONCERNING RELATED APPLICATION(S)

MS RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

*Noted i.
Oct 2004
TH*

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09/945507	August 30, 2001	1303.014US1	FLASH MEMORY WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS
09/945395	August 30, 2001	1303.019US1	DRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY INSULATORS
09/943134	August 30, 2001	1303.020US1	PROGRAMMABLE ARRAY LOGIC OR MEMORY DEVICES WITH ASYMMETRICAL TUNNEL BARRIERS
09/945498	August 30, 2001	1303.024US1	INTEGRATED CIRCUIT MEMORY DEVICE AND METHOD
09/945512	August 30, 2001	1303.027US1	IN SERVICE PROGRAMMABLE LOGIC ARRAYS WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 10/081818

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Title: ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS

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09/945554	August 30, 2001	1303.028US1	SRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY INSULATORS
09/945500	August 30, 2001	1303.029US1	PROGRAMMABLE MEMORY ADDRESS AND DECODE CIRCUITS WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS
10/028001	December 20, 2001	1303.035US1	PROGRAMMABLE ARRAY LOGIC OR MEMORY WITH P-CHANNEL DEVICES AND ASYMMETRICAL TUNNEL BARRIERS
10/177096	June 21, 2002	1303.063US1	GRADED COMPOSITION METAL OXIDE TUNNEL BARRIER INTERPOLY INSULATORS
10/789038	February 27, 2004	1303.024US2	INTEGRATED CIRCUIT MEMORY DEVICE AND METHOD
10/783695	February 20, 2004	1303.019US2	DRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY INSULATORS
10/781035	February 18, 2004	1303.063US2	GRADED COMPOSITION METAL OXIDE TUNNEL BARRIER INTERPOLY INSULATORS
10/788810	February 27, 2004	1303.027US2	IN SERVICE PROGRAMMABLE LOGIC ARRAYS WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS
10/819550	April 7, 2004	1303.019US3	DRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY INSULATORS

COMMUNICATION CONCERNING RELATED APPLICATIONS

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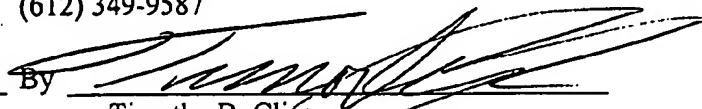
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Name

Amy Moriarty

Signature

